

2SC2315

2SC2316

Silicon NPN Triple Diffused Mesa

☆ Super Beta Transistor

Application Example :
General Purpose

● Outline Drawing 1MT-25(TO220)

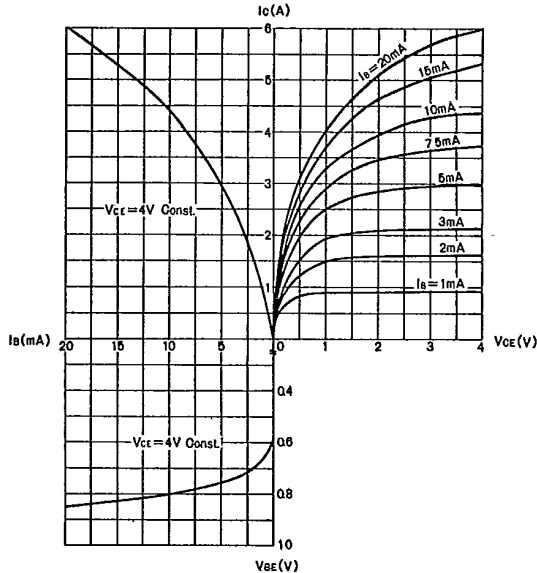
Absolute Maximum Ratings

Symbol	2SC2315	2SC2316	Unit
V_{CB0}	80	100	V
V_{CE0}	60	80	V
V_{EBO}	6		V
I_C	6		A
I_B	3		A
P_C	50 ($T_{FL} = 25^\circ\text{C}$)		W
T_J	150		$^\circ\text{C}$
T_{stg}	-55~+150		$^\circ\text{C}$

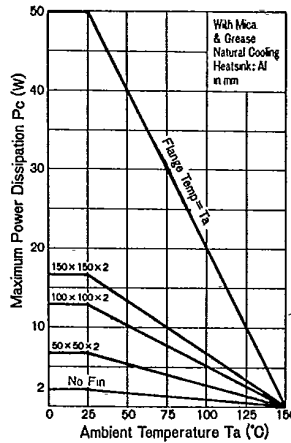
Electrical Characteristics

Symbol	Conditions	2SC2315	2SC2316	Unit
I_{CBO}		100max	100max	μA
	$V_{CB} =$	80	100	V
I_{EBO}	$V_{EB} = 6\text{V}$	1.0max		mA
$V_{(BR)CEO}$	$I_C = 25\text{mA}$	60min	80min	V
h_{FE}	$V_{CE} = 4\text{V}, I_C = 0.5\text{A}$	500min		
$V_{CE(sat)}$	$I_C = 3\text{A}, I_B = 0.06\text{A}$	1.0max		V
f_r	$V_{CE} = 12\text{V}, I_E = -0.5\text{A}$	30typ		MHz

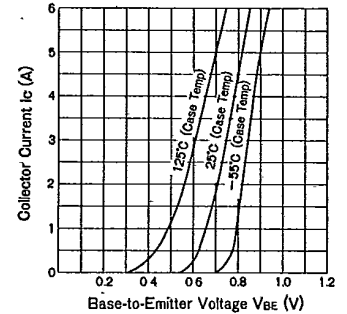
Common Emitter Characteristics (Typical Value)



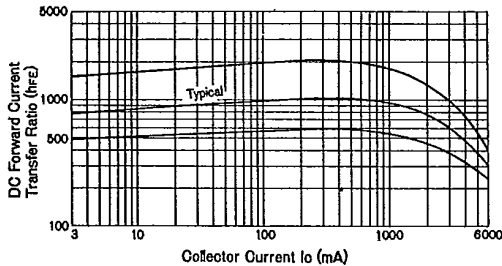
Power Derating



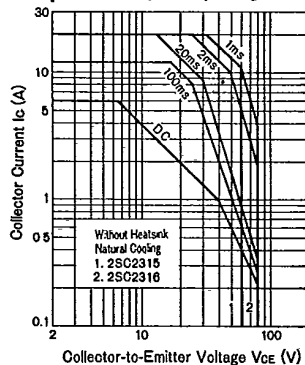
Temperature Characteristics ($V_{CE} = 4\text{V}$ Const.)



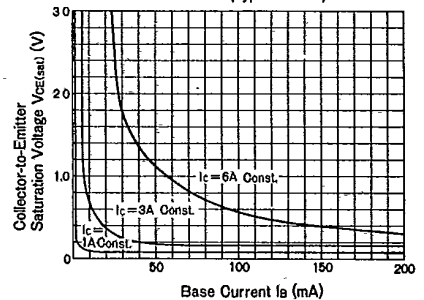
DC Current Gain Characteristics ($V_{CE} = 4\text{V}$ Const.)



Maximum Areas For Safe Operation (ASO) (Single Pulse)



Collector-to-Emitter Saturation Characteristics (Typical Value)



DC Current Gain Temperature Characteristics ($V_{CE} = 4\text{V}$ Const.)

